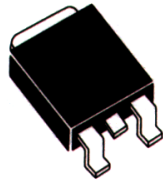




CJD340 NPN  
CJD350 PNP

COMPLEMENTARY SILICON  
POWER TRANSISTOR

**DPAK** POWER!<sup>TM</sup>



DPAK CASE

**Central**<sup>TM</sup>  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CJD340, CJD350 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high voltage general purpose applications.

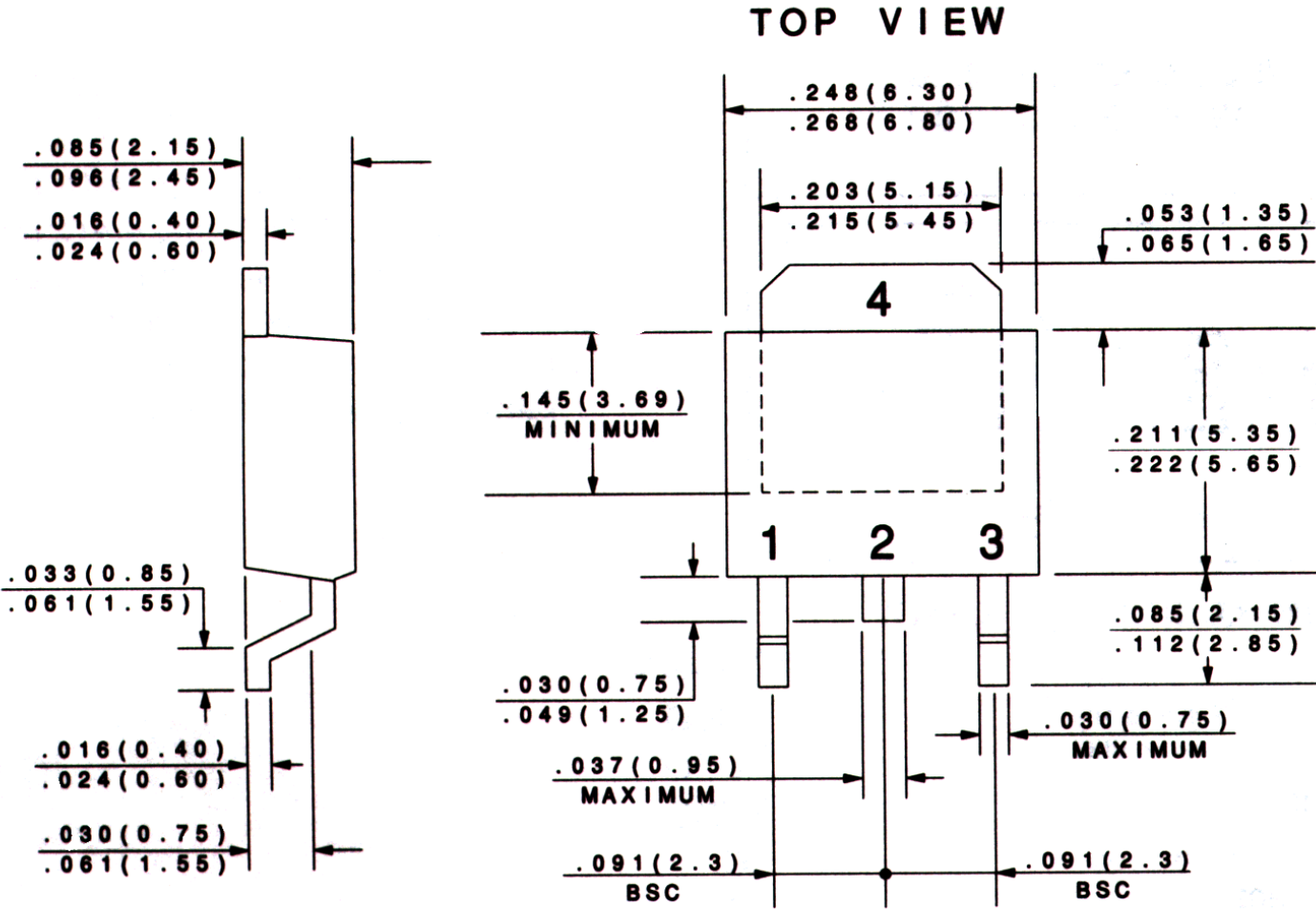
**MAXIMUM RATINGS** ( $T_C=25^\circ\text{C}$ )

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	300	V
Collector-Emitter Voltage	$V_{CEO}$	300	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Continuous Collector Current	$I_C$	500	mA
Peak Collector Current	$I_{CM}$	750	mA
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	15	W
Power Dissipation ( $T_A=25^\circ\text{C}$ )	$P_D$	1.56	W
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JC}$	8.33	$^\circ\text{C/W}$
Thermal Resistance	$\theta_{JA}$	80.1	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=300\text{V}$		100	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=3.0\text{V}$		100	$\mu\text{A}$
$BV_{CEO}$	$I_C=1.0\text{mA}$	300		V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=50\text{mA}$	30	240	

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR